L Number	Hits	Search Text	T DB	Time of the second
1	1210	(ion adj implanter) and substrate	DB .	Time stamp
	1210	(torr adj implanter) and substrate	USPAT;	2004/05/13 14:48
	•	•	US-PGPUB;	,
		ia.	EPO; JPO;	
2	1080	((ion adj implanter) and substrate) and semiconductor	IBM_TDB	2004/05/40 44 45
-	. 1000	(Non adj implanter) and substrate) and semiconductor	USPAT;	2004/05/13 14:48
		V	US-PGPUB;	
			EPO; JPO;	
3	0	(((ion adj implanter) and substrate) and semiconductor) and	IBM_TDB	2004/07/10
		((shadow adj jig)	USPAT;	2004/05/13 14:49
		(Shadow adj jig)	US-PGPUB;	
	•	•	EPO; JPO;	
4	50	(//ion adi implantor) and substrate) and assistant at a last	IBM_TDB	1
'	. 30	(((ion adj implanter) and substrate) and semiconductor) and shadow	USPAT;	2004/05/13 15:16
1		SilduOW	US-PGPUB;	,
		·	EPO; JPO;	
5	13	////ion odd incolors > and a trib to > .	IBM_TDB	,
	13	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:10
		and shadow) and rotat\$3	US-PGPUB;	
			EPO; JPO;	
	50		IBM_TDB	
6	50	((ion adj implanter) and substrate) and shadow	USPAT;	2004/05/13 15:06
,	•		US-PGPUB;	
			EPO; JPO;	
	7		IBM_TDB	
7	/	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:10
	.1	and shadow) and tilt\$3	US-PGPUB;	. •
			EPO; JPO;	,
<u>.</u>			IBM_TDB	*
8	34	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:12
"		and shadow) and (dosage or dose)	US-PGPUB;	
	l:		EPO; JPO;	, ,
,	: :-!		IBM_TDB	The state of the s
9	14	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:12
		and shadow) and (ion near4 (dosage or dose))	US-PGPUB;	
	-2.		EPO; JPO;	
			IBM_TDB	
10	16	((ion adj implanter) and substrate) and (shadow near4	USPAT;	2004/05/13 15:18
	·	substrate)	US-PGPUB;	
	*	<i>,</i> ~	EPO; JPO;	
		41	IBM_TDB	100

L Number	Hits	Search Text	DB	Time stamp
1 .	23	"5343047" "5841969"	USPAT;	2004/05/13 17:46
			US-PGPUB;	200 1/05/15 17.40
			EPO; JPO;	
			IBM_TDB	
-	1210	(ion adj implanter) and substrate	USPAT;	2004/05/13 14:48
· ·	1		US-PGPUB;	200 1/05/15 11.40
		·	EPO; JPO;	
			IBM_TDB	
	1080	((ion adj implanter) and substrate) and semiconductor	USPAT;	2004/05/13 14:48
	,	, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	255.,657.25 2 11.16
			EPO; JPO;	
	v.		IBM_TDB	, .
-	0	(((ion adj implanter) and substrate) and semiconductor) and	USPAT;	2004/05/13 14:49
	1	(shadow adj jig)	US-PGPUB;	
	· ·		EPO; JPO;	
		•	IBM_TDB	
-	50	(((ion adj implanter) and substrate) and semiconductor) and	USPAT;	2004/05/13 15:16
		shadow	US-PGPUB;	
			EPO; JPO;	1"
•			IBM_TDB	
-	13	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:10
		and shadow) and rotat\$3	US-PGPUB;	, ,
	,		EPO; JPO;	
			IBM_TDB	,
-	50	((ion adj implanter) and substrate) and shadow	USPAT;	2004/05/13 15:06
	•		US-PGPUB;	
			EPO; JPO;	
	:		IBM_TDB	
-	7	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:10
		and shadow) and tilt\$3	US-PGPUB;	
			EPO; JPO;	
000		remark to the second of the se	IBM_TDB	
-	34	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:12
. ·		and shadow) and (dosage or dose)	US-PGPUB;	-
			EPO; JPO;	
_	14	((((ion adi implantos) and substrate) and applicate ()	IBM_TDB	2004/05/20 45 15
	. 19	((((ion adj implanter) and substrate) and semiconductor)	USPAT;	2004/05/13 15:19
		and shadow) and (ion near4 (dosage or dose))	US-PGPUB;	ľ
			EPO; JPO;	+
	16	((ion adj implanter) and substrate) and (shadow near4	IBM_TDB	2004/05/42 45:40
	10	substrate)	USPAT;	2004/05/13 15:18
*			US-PGPUB;	
		· ·	EPO; JPO;	
	13	(((ion adj implanter) and substrate) and semiconductor) and	IBM_TDB	2004/05/42 45:45
	15	(beam near4 (blanking or intercepting))	USPAT;	2004/05/13 15:46
· · ·		(Seam hear I (Blanking of intercepting))	US-PGPUB;	`
			EPO; JPO;	, · ·
·		•	IBM_TDB	